

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	"6433842".pn.	USPAT	OR	OFF	2008/04/11 23:59
L3	1	"6081308".pn.	USPAT	OR	OFF	2008/04/12 00:00
L4	46	("3893945" "5162933" "5585647" "5614728" "5621556" "5731856" "5739877" "5756372" "5821622" "5844647" "5852481" "5858807").PN. OR ("6081308").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/04/12 00:02
L5	9	257/E21.19	US-PGPUB; USPAT; USOCR	OR	OFF	2008/04/12 00:22
L6	9	257/E21.19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:23
L7	3	257/E23.017	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:23
L8	20	257/E29.137	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:24
L9	87	257/E29.151	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:24

L10	4393	257/59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:25
L11	3853	257/72	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:30
L12	290	(semiconductor or die or dice or chip or IC) and gate near wire and gate near line and gate near pad	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/12 00:40
L13	286	(semiconductor or die or dice or chip or IC) and gate near wire and gate near line and gate near pad and gate near electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/12 00:40
L14	178	(semiconductor or die or dice or chip or IC) and gate near wire and gate near line and gate near pad and gate near electrode and ("Al" or aluminum) with gate near wire	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/12 00:41
L16	1583	257/763	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:52
L17	826	257/765	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:53
L18	1949	438/30	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 01:10

L19	2035	349/42	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 01:23
L20	2127	349/139	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 01:39
L21	516	349/147	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 01:54
L22	63	257/E27.111	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 01:55
L23	2	"20040140575"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 02:00
L24	13	257/E29.147	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 02:02
L25	3462	257/784	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 02:03
L26	480	349/46	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 02:25

L27	4507	438/149	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 02:33
L28	3546	438/151	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 02:52
S1	1	"6696324".pn.	USPAT	OR	OFF	2007/12/21 21:21
S2	28	("5185294" "5289030" "5313090" "5340761" "5403772" "5573959" "5677240" "5734177" "5837619" "5969377" "6017779" "6043512" "6159779" "6218206" "6274412" "6287899" "6338988" "6340610" "6362028" "6395586").PN. OR ("6696324").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/21 21:28
S3	3	"5978058".pn. or "6444296".pn. or "5181132".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/21 21:30
S4	73	257/E29.151	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/25 17:59
S5	82	257/E51.005	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/25 18:00

S6	3698	257/72	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/25 18:02
S7	1173	257/208	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/25 18:28
S8	819	257/765	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/25 18:28
S9	10	(semiconductor or die or dice or chip or IC) and pad near ("Al" or aluminum) and ("TFT" or thin near film near transistor) and gate and gate near (insulat \$3 or dielectric) and (transparent\$3 or translucent\$3) near (conduct\$3)	USPAT	OR	ON	2007/12/25 18:53
S10	151	(semiconductor or die or dice or chip or IC) and (pad or wir\$3) near ("Al" or aluminum) and ("TFT" or thin near film near transistor) and gate and gate near (insulat \$3 or dielectric) and (transparent\$3 or translucent\$3) near (conduct\$3)	USPAT	OR	ON	2007/12/25 19:37
S11	43	("5478766" "5686976" "5844255" "5852488" "6146796" "6156583" "6172733").PN. OR ("6255130").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/25 19:34

S12	779	(semiconductor or die or dice or chip or IC) and (pad or wir\$3 or metal) near ("Al" or aluminum) and ("TFT" or thin near film near transistor) and gate and gate near (insulat\$3 or dielectric) and (transparent\$3 or translucent\$3) near (conduct\$3)	USPAT	OR	ON	2007/12/25 20:10
S13	628	S12 not S10	USPAT	OR	ON	2007/12/25 20:05
S14	1	"6008065".pn.	USPAT	OR	ON	2007/12/25 20:06
S15	227	(semiconductor or die or dice or chip or IC) and (pad or wir\$3 or metal) near ("Al" or aluminum) same (cap\$4 or cover\$3 or coat\$3 or plat\$3 or second or upper or top) with ("Al" or aluminum) and ("TFT" or thin near film near transistor) and gate and gate near (insulat\$3 or dielectric) and (transparent\$3 or translucent\$3) near (conduct\$3)	USPAT	OR	ON	2007/12/25 20:12

4/12/08 2:56:59 AM

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